

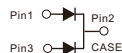
FEATURES

- Power pack
- Metal silicon junction ,majority carrier conduction
- Guard ring for overvoltage protection
- Low power loss ,high efficiency
- High current capability ,low forward voltage drop
- High forward surge capability
- High frequency operation
- Meets MSL Level 1, per J-STD-020, LF MAX peak of 245°C (for TO-263 package)
- Solder bath temperature 275°C maximum, 10s, per JESD22-B106 (for TO-220AB and ITO-220AB package)
- Component in accordance to RoHS 2011/65/EU



TO-220AB

SR20120SLCT



ITO-220AB

SRF20120SLCT



TO-263

SR20120SLD1



MECHANICAL DATA

- Case: JEDEC TO-220AB、ITO-220AB、TO-263
- Molding compound meets UL94V-0 flammability rating
- Terminals: Lead solderable per J-STD-002 and JESD22-B102
- Polarity: As marked
- Mounting Torque: 10 in-lbs maximum

TYPICAL APPLICATIONS

For use in low voltage ,high frequency inverters ,DC/DC converters, free wheeling ,and polarity protection applications

MAXIMUM RATINGS

(Ratings at 25°C ambient temperature unless otherwise specified)

Parameter	Symbol	SR20120SLCT, SRF20120SLCT,SR20120SLD1	Unit
Maximum repetitive peak reverse voltage	V_{RRM}	120	V
Maximum average forward rectified current (see fig.1)	Per leg	10.0	A
	Total device	20.0	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method at rated TL)	I_{FSM}	250	A
Peak repetitive reverse current per diode at $t_p=2 \mu s$ 1KHz	I_{RRM}	0.5	A
Operating junction and Storage temperature range	T_J, T_{stg}	-55 to+150	°C
Isolation voltage (ITO-220AB only) from terminals to heatsink $t=1$ min	V_{AC}	1500	V

PRIMARY CHARACTERISTICS	
$I_F(AV)$	2×10A
V_{RRM}	120V
I_{FSM}	250A
V_f at $I_F=10.0A$,Per leg,25°C	0.70V
I_t	11 μA
$T_J(MAX)$	150°C
Package	TO-220AB, ITO-220AB, TO-263
Diode variations	Common cathode

RATINGS AND CHARACTERISTIC OF SR20120SLCT,SRF20120SLCT,SR20120SLD1

ELECTRICAL CHARACTERISTICS (T_A=25°C Unless otherwise noted)

Parameter	Test Conditions		Symbol	TYP.	MAX.	Unit
Instantaneous forward voltage	Per leg I _F =10.0A	T _A =25°C	V _F ¹⁾	0.70	0.75	V
		T _A =100°C		0.63	–	
		T _A =125°C		0.59	–	
	Per leg I _F =5.0A	T _A =25°C		0.55	–	
		T _A =100°C		0.52	–	
		T _A =125°C		0.50	–	
Reverse current	V _R =120V	T _A =25°C	I _R ²⁾	11	50	μA
		T _A =100°C		2.5	–	mA
		T _A =125°C		10	–	
Typical junction capacitance	4V, 1MHz		C _J	570		pF

Notes: 1.Pulse test: 300 μs pulse width,1% duty cycle

2.Pulse test: pulse width≤40ms

THERMAL CHARACTERISTICS (T_A=25°C Unless otherwise noted)

Parameter	Symbol	SR20120SLCT	SRF20120SLCT	SR20120SLD1	Unit
Typical thermal resistance ³⁾	R _{θJC}	2.5	4.5	2.5	°C/W

3.Thermal resistance from junction to case

AVAILABLE PACK INFORMATION

Product code	Pack	Box Size L×W×H(mm)	Quantity (pcs/box)	Carton SizeL×W×H(mm)	Quantity (box/carton)
SR20120SLCT-TO-220AB	P/T	558×148×38	1000	565×225×170	5
SRF20120SLCT-ITO-220AB	P/T	558×148×38	1000	565×225×170	5
SR20120SLD1-TO-263	P/T	558×148×38	1000	565×225×170	5

RATINGS AND CHARACTERISTIC OF SR20120SLCT,SRF20120SLCT,SR20120SLD1

FIG.1-FORWARD CURRENT DERATING CURVE

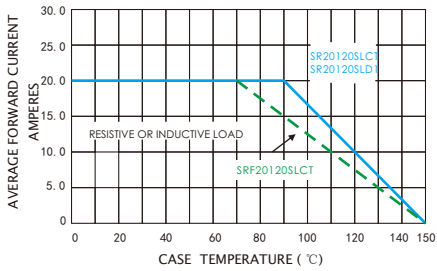


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

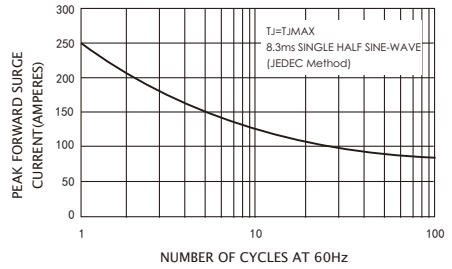


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

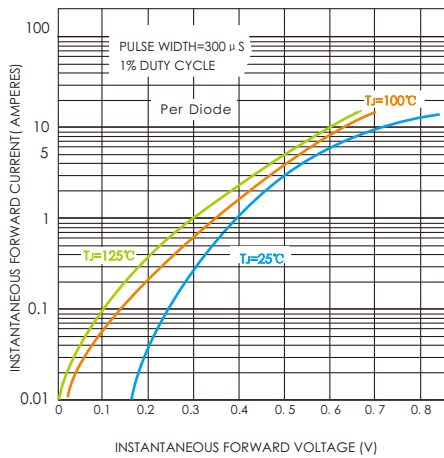


FIG.4-TYPICAL REVERSE CHARACTERISTICS

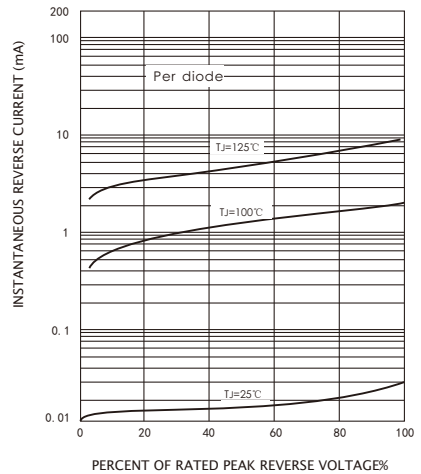
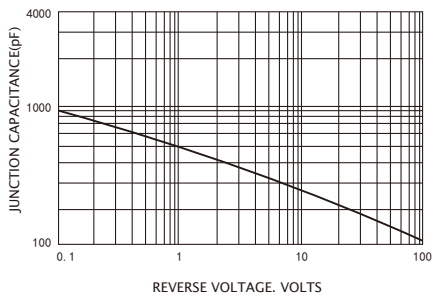
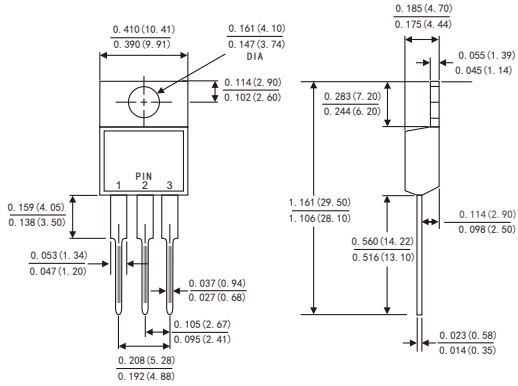


FIG.5-TYPICAL JUNCTION CAPACITANCE

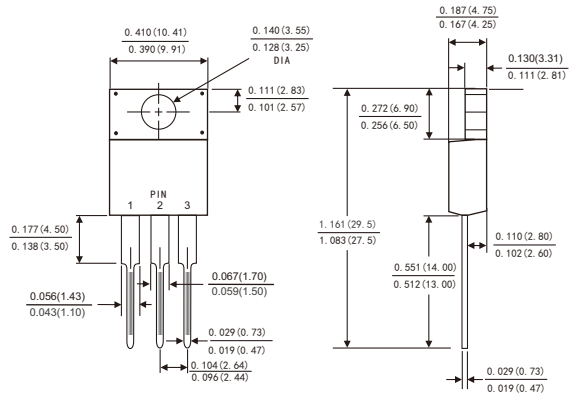


PACKAGE OUTLINE DIMENSIONS

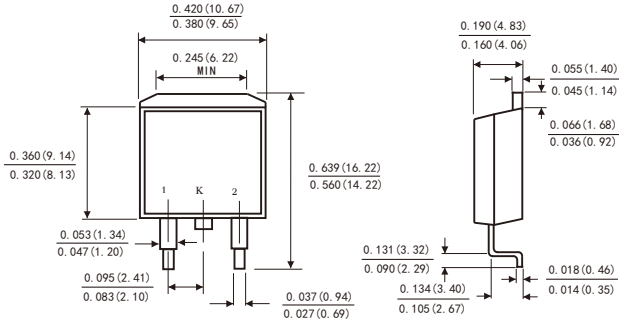
TO-220AB



ITO-220AB

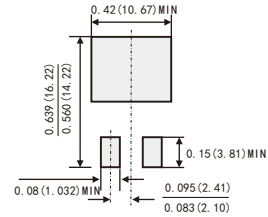


TO-263



Suggested Pad Layout

(TO-263)



Dimensions in inches and (millimeters)